

General Description

The WST6401 is the highest performance trench P-ch MOSFET with extreme high cell density , which provide excellent R_{DS(on)} and gate charge for most of the small power switching and load switch applications.

The WST6401 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent C_{dv/dt} effect decline
- Green Device Available

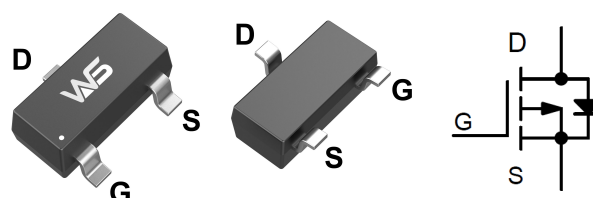
Product Summary

| BVDSS | R _{DS(on)} | I _D |
|-------|---------------------|----------------|
| -20V | 135mΩ | -2.5A |

Applications

- High Frequency Point-of-Load Synchronous Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23N Pin Configuration



Absolute Maximum Ratings

| Symbol | Parameter | Rating | Units |
|--------------------------------------|--|------------|-------|
| V _{DS} | Drain-Source Voltage | -20 | V |
| V _{GS} | Gate-Source Voltage | ±12 | V |
| I _D @T _c =25°C | Continuous Drain Current, V _{GS} @ -4.5V ¹ | -2.5 | A |
| I _D @T _c =70°C | Continuous Drain Current, V _{GS} @ -4.5V ¹ | -1.9 | A |
| I _{DM} | Pulsed Drain Current ² | -10 | A |
| P _D @T _A =25°C | Total Power Dissipation ³ | 0.7 | W |
| T _{STG} | Storage Temperature Range | -55 to 150 | °C |
| T _J | Operating Junction Temperature Range | -55 to 150 | °C |

Thermal Data

| Symbol | Parameter | Typ. | Max. | Unit |
|------------------|--|------|------|------|
| R _{θJA} | Thermal Resistance Junction-ambient ¹ | --- | 178 | °C/W |
| R _{θJC} | Thermal Resistance Junction-Case ¹ | --- | 80 | °C/W |

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-------------------------------------|--|--|------|--------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =-250uA | -20 | --- | --- | V |
| ΔBV _{DSS} /ΔT _J | BVDSS Temperature Coefficient | Reference to 25°C, I _D =-1mA | --- | -0.016 | --- | V/°C |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =-4.5V, I _D =-2A | --- | 135 | 165 | mΩ |
| | | V _{GS} =-2.5V, I _D =-1A | --- | 150 | 186 | |
| | | V _{GS} =-1.8V, I _D =-1.5A | --- | 250 | 355 | |
| V _{GS(th)} | Gate Threshold Voltage | V _{GS} =V _{DS} , I _D =-250uA | -0.5 | -0.7 | -1.2 | V |
| ΔV _{GS(th)} | V _{GS(th)} Temperature Coefficient | | --- | 3.97 | --- | mV/°C |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =-16V, V _{GS} =0V, T _J =25°C | --- | --- | -1 | uA |
| | | V _{DS} =-16V, V _{GS} =0V, T _J =55°C | --- | --- | -5 | |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =±8V, V _{DS} =0V | --- | --- | ±100 | nA |
| g _{fs} | Forward Transconductance | V _{DS} =-5V, I _D =-2A | --- | . | --- | S |
| R _g | Gate Resistance | V _{DS} =0V, V _{GS} =0V, f=1MHz | --- | 13.1 | --- | Ω |
| Q _g | Total Gate Charge (-4.5V) | V _{DS} =-15V, V _{GS} =-4.5V, I _D =-2A | --- | 3.0 | --- | nC |
| Q _{gs} | Gate-Source Charge | | --- | 0.5 | --- | |
| Q _{gd} | Gate-Drain Charge | | --- | 0.8 | --- | |
| T _{d(on)} | Turn-On Delay Time | V _{DD} =-15V, V _{GS} =-4.5V, R _G =3.0Ω I _D =-2A | --- | 10 | --- | ns |
| T _r | Rise Time | | --- | 5.0 | --- | |
| T _{d(off)} | Turn-Off Delay Time | | --- | 21 | --- | |
| T _f | Fall Time | | --- | 7 | --- | |
| C _{iss} | Input Capacitance | V _{DS} =-15V, V _{GS} =0V, f=1MHz | --- | 290 | --- | pF |
| C _{oss} | Output Capacitance | | --- | 60 | --- | |
| C _{rss} | Reverse Transfer Capacitance | | --- | 34 | --- | |

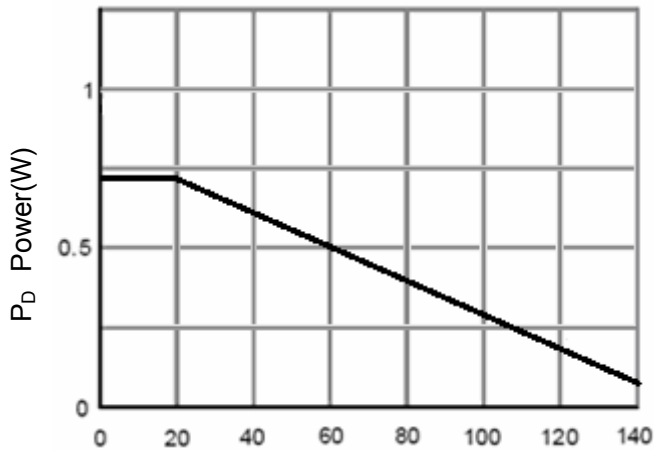
Diode Characteristics

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|-----------------|--|--|------|------|------|------|
| I _S | Continuous Source Current ^{1,4} | V _G =V _D =0V, Force Current | --- | --- | -2.5 | A |
| I _{SM} | Pulsed Source Current ^{2,4} | | --- | --- | -10 | A |
| V _{SD} | Diode Forward Voltage ² | V _{GS} =0V, I _S =-1A, T _J =25°C | --- | --- | -1.2 | V |

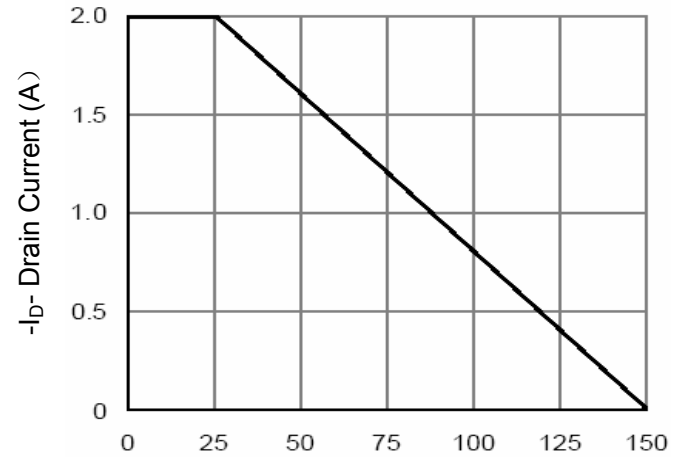
Notes:

- 1、Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2、Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3、Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
- 4、Guaranteed by design, not subject to production

Typical Characteristics



T_J-Junction Temperature(°C)
Figure 1 Power Dissipation



T_J-Junction Temperature(°C)
Figure 2 Drain Current

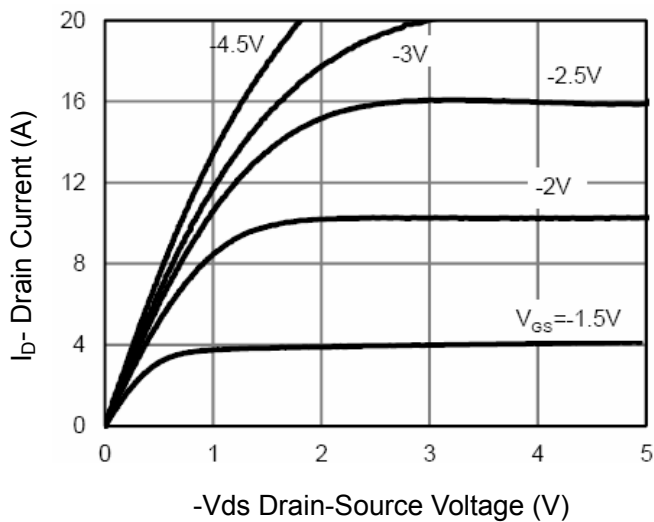


Figure 3 Output Characteristics

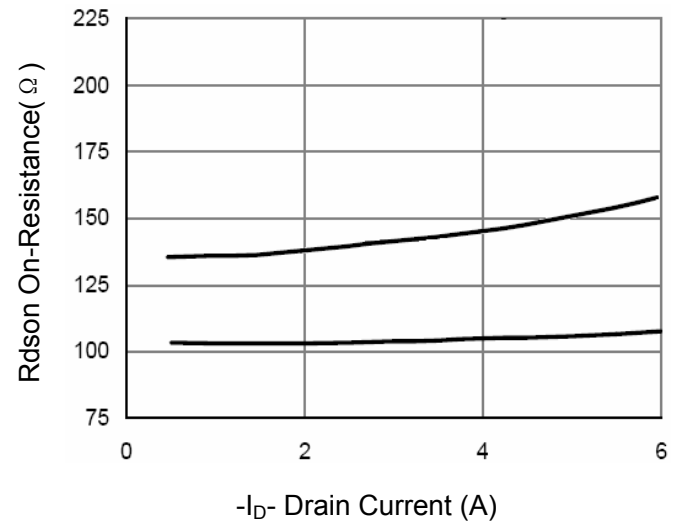


Figure 4 Drain-Source On-Resistance

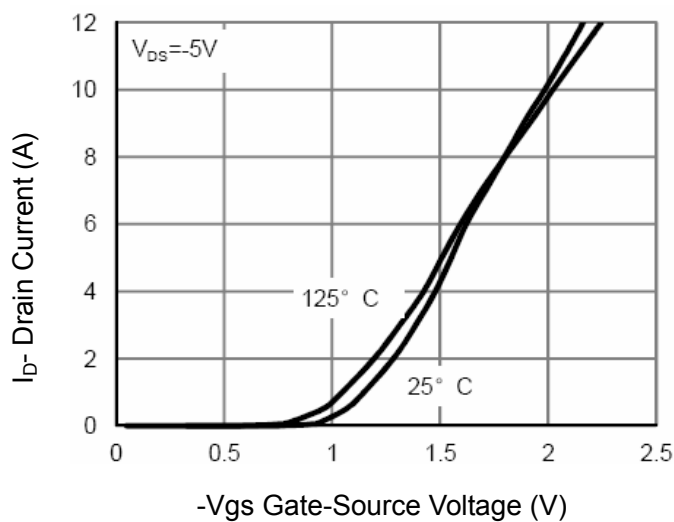


Figure 5 Transfer Characteristics

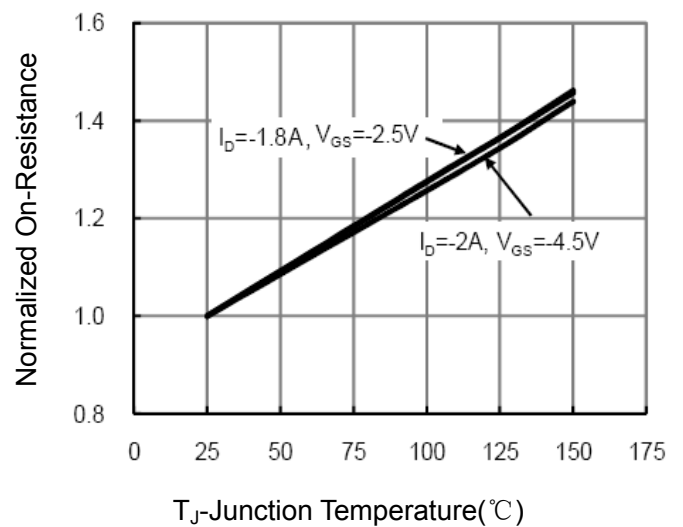


Figure 6 Drain-Source On-Resistance

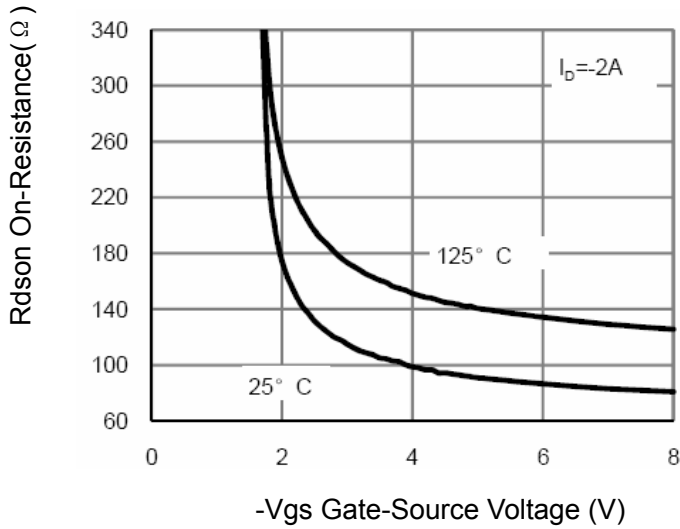


Figure 7 Rdson vs Vgs

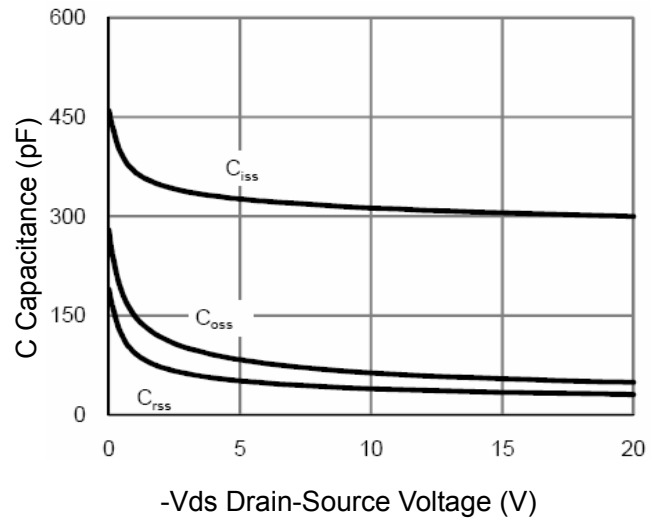


Figure 8 Capacitance vs Vds

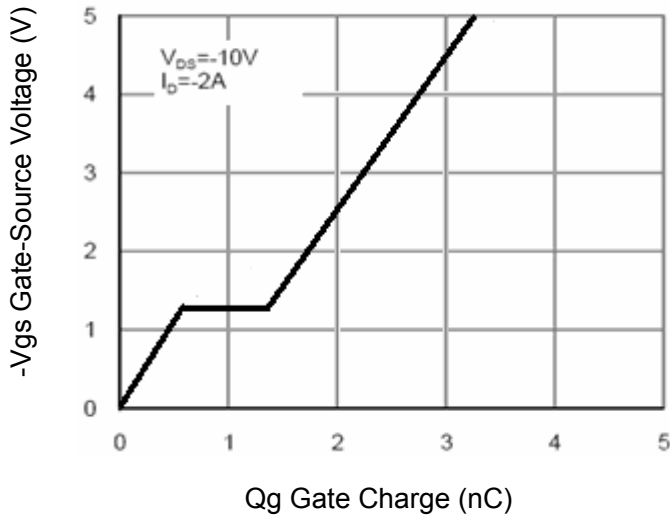


Figure 9 Gate Charge

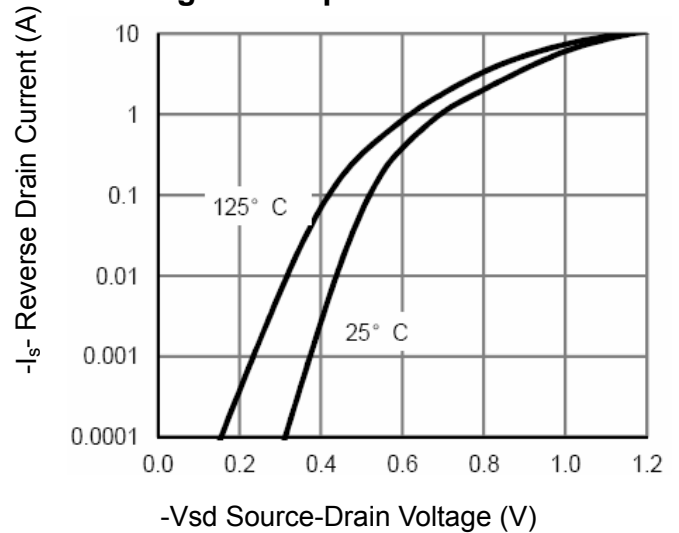


Figure 10 Source- Drain Diode Forward

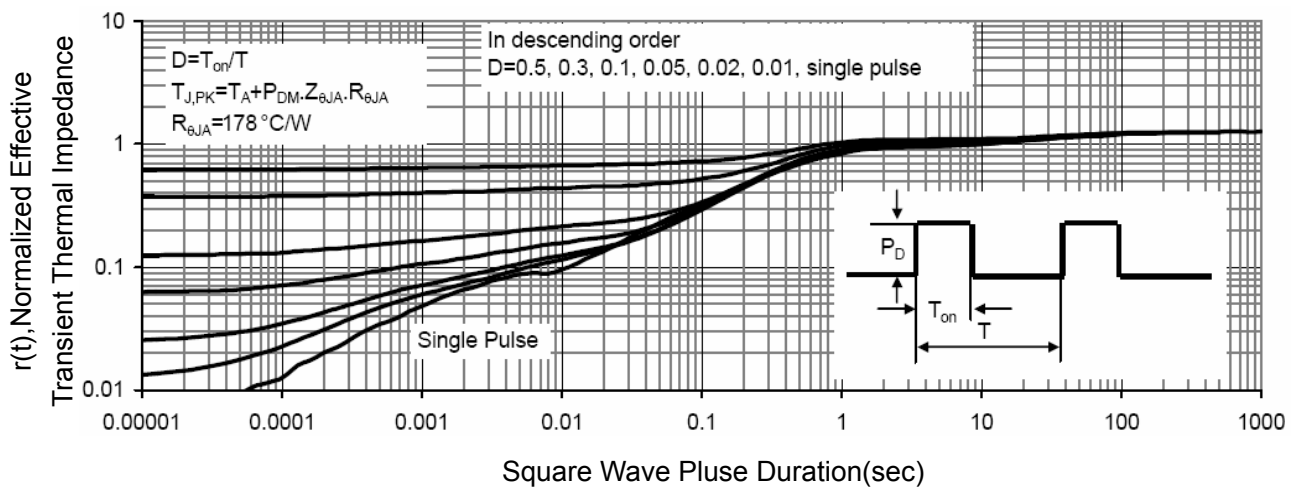


Figure 11 Normalized Maximum Transient Thermal Impedance



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